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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	87
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	40K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 39x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f303vct6tr

3.22 Serial peripheral interface (SPI)/Inter-integrated sound interfaces (I2S)

Up to three SPIs are able to communicate up to 18 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame size is configurable from 4 bits to 16 bits.

Two standard I2S interfaces (multiplexed with SPI2 and SPI3) supporting four different audio standards can operate as master or slave at half-duplex and full duplex communication modes. They can be configured to transfer 16 and 24 or 32 bits with 16-bit or 32-bit data resolution and synchronized by a specific signal. Audio sampling frequency from 8 kHz up to 192 kHz can be set by 8-bit programmable linear prescaler. When operating in master mode it can output a clock for an external audio component at 256 times the sampling frequency.

Refer to *Table 9* for the features available in SPI1, SPI2 and SPI3.

Table 9. STM32F303xB/STM32F303xC SPI/I2S implementation

SPI features(1)	SPI1	SPI2	SPI3
Hardware CRC calculation	X	X	X
Rx/Tx FIFO	X	X	X
NSS pulse mode	X	X	X
I2S mode	-	X	X
TI mode	X	X	X

1. **X = supported.**

3.23 Controller area network (CAN)

The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

3.24 Universal serial bus (USB)

The STM32F303xB/STM32F303xC devices embed an USB device peripheral compatible with the USB full-speed 12 Mbs. The USB interface implements a full-speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and suspend/resume support. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator). The USB has a dedicated 512-bytes SRAM memory for data transmission and reception.

Table 10. Capacitive sensing GPIOs available on STM32F303xB/STM32F303xC devices

Group	Capacitive sensing signal name	Pin name	Group	Capacitive sensing signal name	Pin name
1	TSC_G1_IO1	PA0	5	TSC_G5_IO1	PB3
	TSC_G1_IO2	PA1		TSC_G5_IO2	PB4
	TSC_G1_IO3	PA2		TSC_G5_IO3	PB6
	TSC_G1_IO4	PA3		TSC_G5_IO4	PB7
2	TSC_G2_IO1	PA4	6	TSC_G6_IO1	PB11
	TSC_G2_IO2	PA5		TSC_G6_IO2	PB12
	TSC_G2_IO3	PA6		TSC_G6_IO3	PB13
	TSC_G2_IO4	PA7		TSC_G6_IO4	PB14
3	TSC_G3_IO1	PC5	7	TSC_G7_IO1	PE2
	TSC_G3_IO2	PB0		TSC_G7_IO2	PE3
	TSC_G3_IO3	PB1		TSC_G7_IO3	PE4
	TSC_G3_IO4	PB2		TSC_G7_IO4	PE5
4	TSC_G4_IO1	PA9	8	TSC_G8_IO1	PD12
	TSC_G4_IO2	PA10		TSC_G8_IO2	PD13
	TSC_G4_IO3	PA13		TSC_G8_IO3	PD14
	TSC_G4_IO4	PA14		TSC_G8_IO4	PD15

Table 11. No. of capacitive sensing channels available on STM32F303xB/STM32F303xC devices

Analog I/O group	Number of capacitive sensing channels		
	STM32F303Vx	STM32F303Rx	STM32F303Cx
G1	3	3	3
G2	3	3	3
G3	3	3	2
G4	3	3	3
G5	3	3	3
G6	3	3	3
G7	3	0	0
G8	3	0	0
Number of capacitive sensing channels	24	18	17

3.27 Development support

3.27.1 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP Interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

The JTAG TMS and TCK pins are shared respectively with SWDIO and SWCLK and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

3.27.2 Embedded trace macrocell™

The ARM embedded trace macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F303xB/STM32F303xC through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using a high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer running debugger software. TPA hardware is commercially available from common development tool vendors. It operates with third party debugger software tools.

Table 12. Legend/abbreviations used in the pinout table

Name		Abbreviation	Definition
Pin name		Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type		S	Supply pin
		I	Input only pin
		I/O	Input / output pin
I/O structure		FT	5 V tolerant I/O
		FTf	5 V tolerant I/O, FM+ capable
		TTa	3.3 V tolerant I/O directly connected to ADC
		TC	Standard 3.3V I/O
		B	Dedicated BOOT0 pin
		RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes		Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers	
	Additional functions	Functions directly selected/enabled through peripheral registers	

Table 13. STM32F303xB/STM32F303xC pin definitions

Pin number				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
WLCSP100	LQFP100	LQFP64	LQFP48					Alternate functions	Additional functions
D6	1	-	-	PE2	I/O	FT	(1)	TRACECK, TIM3_CH1, TSC_G7_IO1, EVENTOUT	-
D7	2	-	-	PE3	I/O	FT	(1)	TRACED0, TIM3_CH2, TSC_G7_IO2, EVENTOUT	-
C8	3	-	-	PE4	I/O	FT	(1)	TRACED1, TIM3_CH3, TSC_G7_IO3, EVENTOUT	-
B9	4	-	-	PE5	I/O	FT	(1)	TRACED2, TIM3_CH4, TSC_G7_IO4, EVENTOUT	-
E7	5	-	-	PE6	I/O	FT	(1)	TRACED3, EVENTOUT	WKUP3, RTC_TAMP3
D8	6	1	1	V_{BAT}	S	-	-	Backup power supply	

Table 13. STM32F303xB/STM32F303xC pin definitions (continued)

Pin number				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
WLCSP100	LQFP100	LQFP64	LQFP48					Alternate functions	Additional functions
B5	90	56	40	PB4	I/O	FT	-	SPI3_MISO, I2S3ext_SD, SPI1_MISO, USART2_RX, TIM3_CH1, TIM16_CH1, TIM17_BKIN, TIM8_CH2N, TSC_G5_IO2, NJTRST, EVENTOUT	-
A6	91	57	41	PB5	I/O	FT	-	SPI3_MOSI, SPI1_MOSI, I2S3_SD, I2C1_SMBA, USART2_CK, TIM16_BKIN, TIM3_CH2, TIM8_CH3N, TIM17_CH1, EVENTOUT	-
B6	92	58	42	PB6	I/O	FTf	-	I2C1_SCL, USART1_TX, TIM16_CH1N, TIM4_CH1, TIM8_CH1,TSC_G5_IO3, TIM8_ETR, TIM8_BKIN2, EVENTOUT	-
C5	93	59	43	PB7	I/O	FTf	-	I2C1_SDA, USART1_RX, TIM3_CH4, TIM4_CH2, TIM17_CH1N, TIM8_BKIN, TSC_G5_IO4, EVENTOUT	-
A7	94	60	44	BOOT0	I	B	-	Boot memory selection	
D5	95	61	45	PB8	I/O	FTf	-	I2C1_SCL, CAN_RX, TIM16_CH1, TIM4_CH3, TIM8_CH2, TIM1_BKIN, TSC_SYNC, COMP1_OUT, EVENTOUT	-
C6	96	62	46	PB9	I/O	FTf	-	I2C1_SDA, CAN_TX, TIM17_CH1, TIM4_CH4, TIM8_CH3, IR_OUT, COMP2_OUT, EVENTOUT	-
B7	97	-	-	PE0	I/O	FT	(1)	USART1_TX, TIM4_ETR, TIM16_CH1, EVENTOUT	-
A8	98	-	-	PE1	I/O	FT	(1)	USART1_RX, TIM17_CH1, EVENTOUT	-
C7	99	63	47	VSS	S	-	-	Ground	
A9, A10, B10, B8	100	64	48	VDD	S	-	-	Digital power supply	

Table 14. Alternate functions for port A (continued)

Port & Pin Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF14	AF15
PA12	-	TIM16_CH1	-	-	-	-	TIM1_CH2N	USART1_RTS_DE	COMP2_OUT	CAN_TX	TIM4_CH2	TIM1_ETR	-	USB_DP	EVENTOUT
PA13	SWDIO-JTMS	TIM16_CH1N	-	TSC_G4_IO3	-	IR_OUT	-	USART3_CTS	-	-	TIM4_CH3	-	-	-	EVENTOUT
PA14	SWCLK-JTCK	-	-	TSC_G4_IO4	I2C1_SDA	TIM8_CH2	TIM1_BKIN	USART2_TX	-	-	-	-	-	-	EVENTOUT
PA15	JTDI	TIM2_CH1_ETR	TIM8_CH1	-	I2C1_SCL	SPI1_NSS	SPI3_NSS, I2S3_WS	USART2_RX	-	TIM1_BKIN	-	-	-	-	EVENTOUT

6.3 Operating conditions

6.3.1 General operating conditions

Table 24. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	72	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	36	
f_{PCLK2}	Internal APB2 clock frequency	-	0	72	
V_{DD}	Standard operating voltage	-	2	3.6	V
V_{DDA}	Analog operating voltage (OPAMP and DAC not used)	Must have a potential equal to or higher than V_{DD}	2	3.6	V
	Analog operating voltage (OPAMP and DAC used)		2.4	3.6	
V_{BAT}	Backup operating voltage	-	1.65	3.6	V
V_{IN}	I/O input voltage	TC I/O	–0.3	V_{DD}+0.3	V
		TTa I/O	–0.3	V_{DDA}+0.3	
		FT and FTf I/O(1)	–0.3	5.5	
		BOOT0	0	5.5	
P_D	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7(2)	WLCSP100	-	500	mW
		LQFP100	-	488	
		LQFP64	-	444	
		LQFP48	-	364	
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation	–40	85	°C
		Low-power dissipation(3)	–40	105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	–40	105	°C
		Low-power dissipation(3)	–40	125	
T_J	Junction temperature range	6 suffix version	–40	105	°C
		7 suffix version	–40	125	

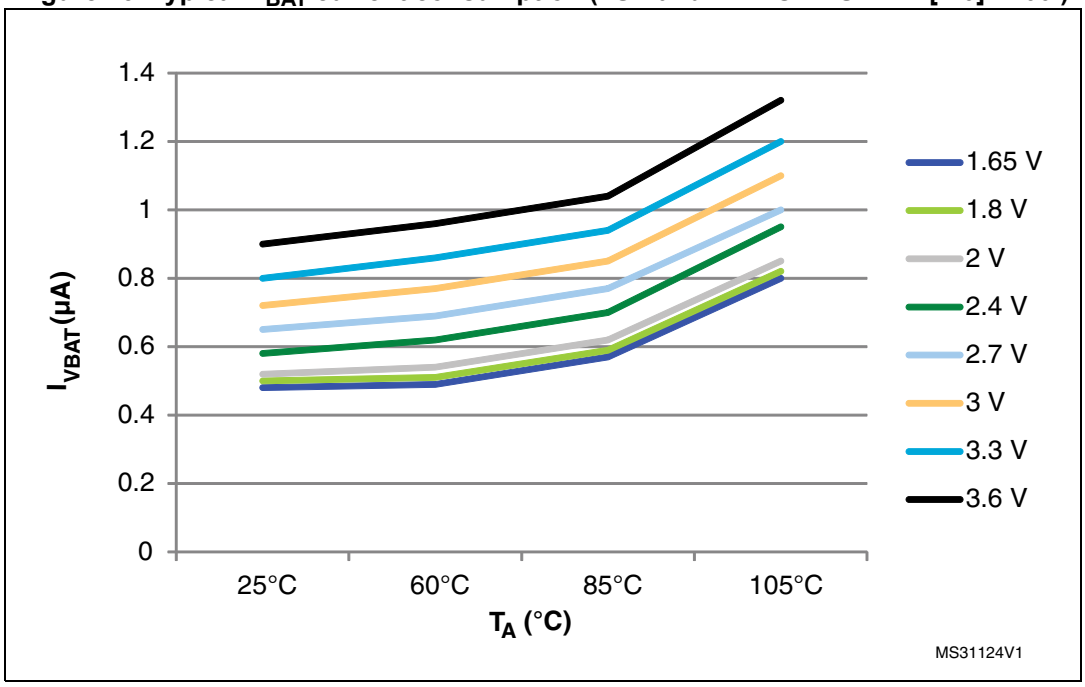
1. To sustain a voltage higher than V_{DD}+0.3 V, the internal pull-up/pull-down resistors must be disabled.
2. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} (see *Section 7.5: Thermal characteristics*).
3. In low-power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (see *Section 7.5: Thermal characteristics*).

Table 34. Typical and maximum current consumption from V_{BAT} supply

Symbol	Para meter	Conditions (1)	Typ @V_{BAT}								Max @V_{BAT} = 3.6 V(2)			Unit
			1.65V	1.8V	2V	2.4V	2.7V	3V	3.3V	3.6V	T_A = 25°C	T_A = 85°C	T_A = 105°C	
I_{DD_VBAT}	Backup domain supply current	LSE & RTC ON; "Xtal mode" lower driving capability; LSEDRV[1:0] = '00'	0.48	0.50	0.52	0.58	0.65	0.72	0.80	0.90	1.1	1.5	2.0	µA
		LSE & RTC ON; "Xtal mode" higher driving capability; LSEDRV[1:0] = '11'	0.83	0.86	0.90	0.98	1.03	1.10	1.20	1.30	1.5	2.2	2.9	

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a CL of 6 pF for typical values.
2. Guaranteed by characterization results.

Figure 13. Typical V_{BAT} current consumption (LSE and RTC ON/LSEDRV[1:0] = '00')



6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

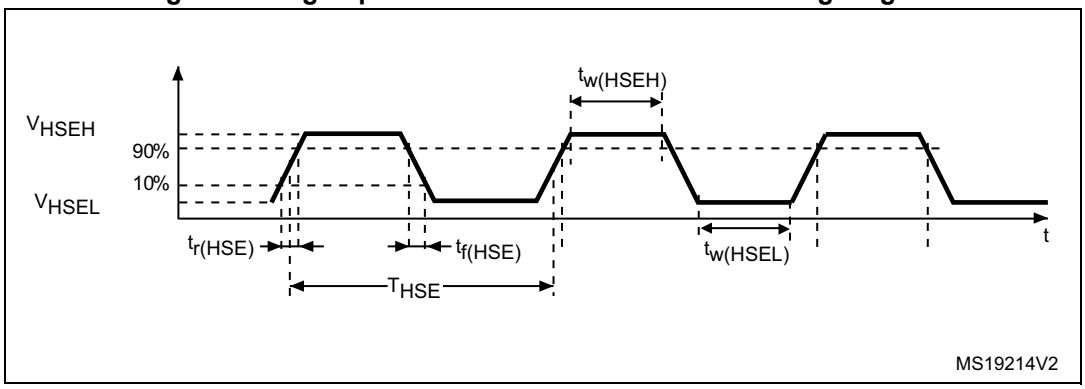
In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 14*.

Table 40. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency(1)	-	1	8	32	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time(1)		15	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time(1)		-	-	20	

1. Guaranteed by design.

Figure 14. High-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 42*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 42. HSE oscillator characteristics

Symbol	Parameter	Conditions(1)	Min(2)	Typ	Max(2)	Unit
f_{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R_F	Feedback resistor	-	-	200		kΩ
I_{DD}	HSE current consumption	During startup(3)	-	-	8.5	mA
		V_{DD}=3.3 V, Rm= 30Ω, CL=10 pF@8 MHz	-	0.4	-	
		V_{DD}=3.3 V, Rm= 45Ω, CL=10 pF@8 MHz	-	0.5	-	
		V_{DD}=3.3 V, Rm= 30Ω, CL=5 pF@32 MHz	-	0.8	-	
		V_{DD}=3.3 V, Rm= 30Ω, CL=10 pF@32 MHz	-	1	-	
		V_{DD}=3.3 V, Rm= 30Ω, CL=20 pF@32 MHz	-	1.5	-	
g_m	Oscillator transconductance	Startup	10	-	-	mA/V
$t_{SU(HSE)}$(4)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by design.
3. This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 50. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8/72 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	**7**	dBµV
			30 to 130 MHz	**20**	
			130 MHz to 1GHz	**27**	
			SAE EMI Level	**4**	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114, ANSI/ESD STM5.3.1 standard.

Table 51. ESD absolute maximum ratings

Symbol	Ratings	Conditions		Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to JESD22-A114		2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1	WLCSP100 package	3	250	
			Packages except WLCSP100	4	500	

1. Guaranteed by characterization results.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 19* and *Figure 20* for standard I/Os.

Figure 19. TC and TTa I/O input characteristics - CMOS port

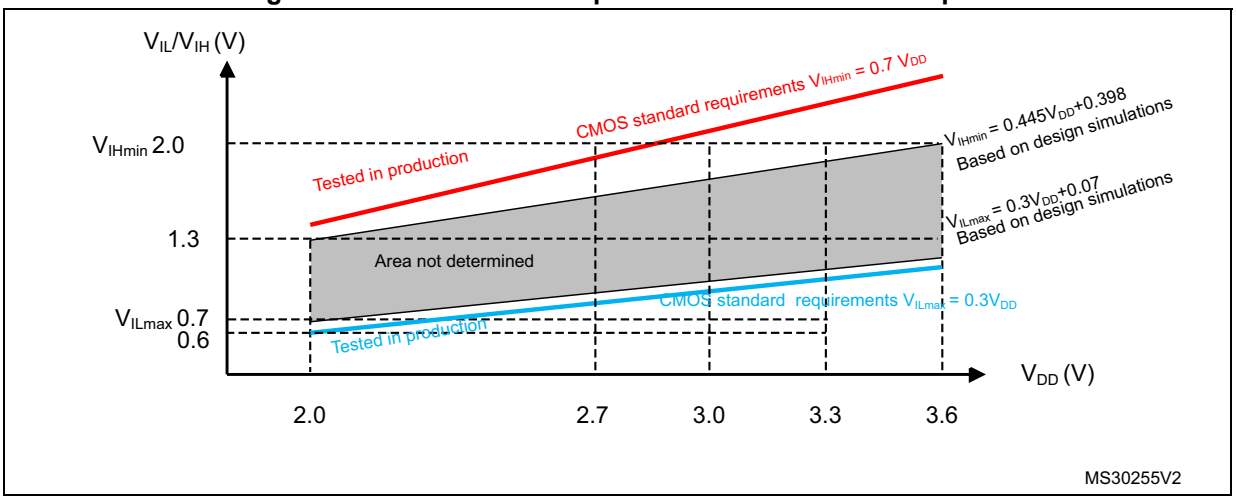
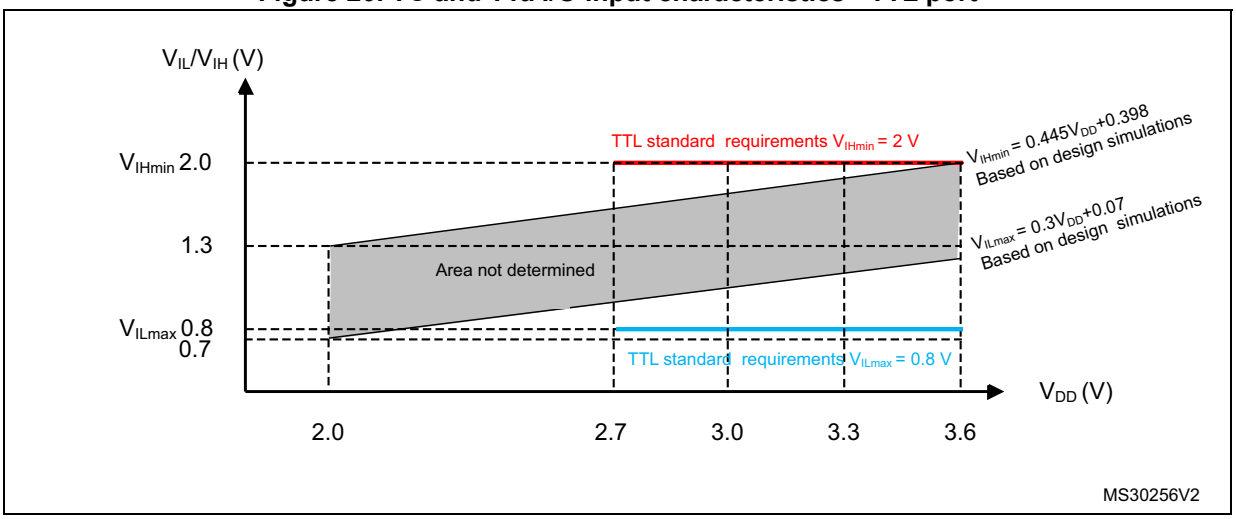


Figure 20. TC and TTa I/O input characteristics - TTL port



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to +/-8 mA, and sink or source up to +/- 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on V_{DD}, plus the maximum Run consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 22*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 22*).

Output voltage levels

Unless otherwise specified, the parameters given in *Table 55* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24*. All I/Os (FT, TTa and TC unless otherwise specified) are CMOS and TTL compliant.

Table 55. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL} (1)	Output low level voltage for an I/O pin	CMOS port(2) I_{IO} = +8 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH} (3)	Output high level voltage for an I/O pin		V_{DD}–0.4	-	
V_{OL} (1)	Output low level voltage for an I/O pin	TTL port(2) I_{IO} = +8 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	
V_{OH} (3)	Output high level voltage for an I/O pin		2.4	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = +20 mA 2.7 V < V_{DD} < 3.6 V	-	1.3	
V_{OH} (3)(4)	Output high level voltage for an I/O pin		V_{DD}–1.3	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = +6 mA 2 V < V_{DD} < 2.7 V	-	0.4	
V_{OH} (3)(4)	Output high level voltage for an I/O pin		V_{DD}–0.4	-	
V_{OLFM+} (1)(4)	Output low level voltage for an FTf I/O pin in FM+ mode	I_{IO} = +20 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 22* and the sum of I_{IO} (I/O ports and control pins) must not exceed $\Sigma I_{IO(PIN)}$.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 22* and the sum of I_{IO} (I/O ports and control pins) must not exceed $\Sigma I_{IO(PIN)}$.
4. Data based on design simulation.

6.3.18 ADC characteristics

Unless otherwise specified, the parameters given in *Table 68* to *Table 70* are guaranteed by design, with conditions summarized in *Table 24*.

Table 68. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage for ADC	-	2	-	3.6	V
I_{DDA}	ADC current consumption on VDDA pin (see *Figure 32*)	Single-ended mode, 5 MSPS	-	907	1033.0	µA
		Single-ended mode, 1 MSPS	-	194	285.5	
		Single-ended mode, 200 KSPS	-	51.5	70	
		Differential mode, 5 MSPS	-	887.5	1009	
		Differential mode, 1 MSPS	-	212	285	
		Differential mode, 200 KSPS	-	51	69.5	
V_{REF+}	Positive reference voltage	-	2	-	V_{DDA}	V
V_{REF-}	Negative reference voltage	-	-	0	-	
I_{REF}	ADC current consumption on VREF+ pin (see *Figure 33*)	Single-ended mode, 5 MSPS	-	104	139	µA
		Single-ended mode, 1 MSPS	-	20.4	37	
		Single-ended mode, 200 KSPS	-	3.3	11.3	
		Differential mode, 5 MSPS	-	174	235	
		Differential mode, 1 MSPS	-	34.6	52.6	
		Differential mode, 200 KSPS	-	6	13.6	

Figure 32. ADC typical current consumption on VDDA pin

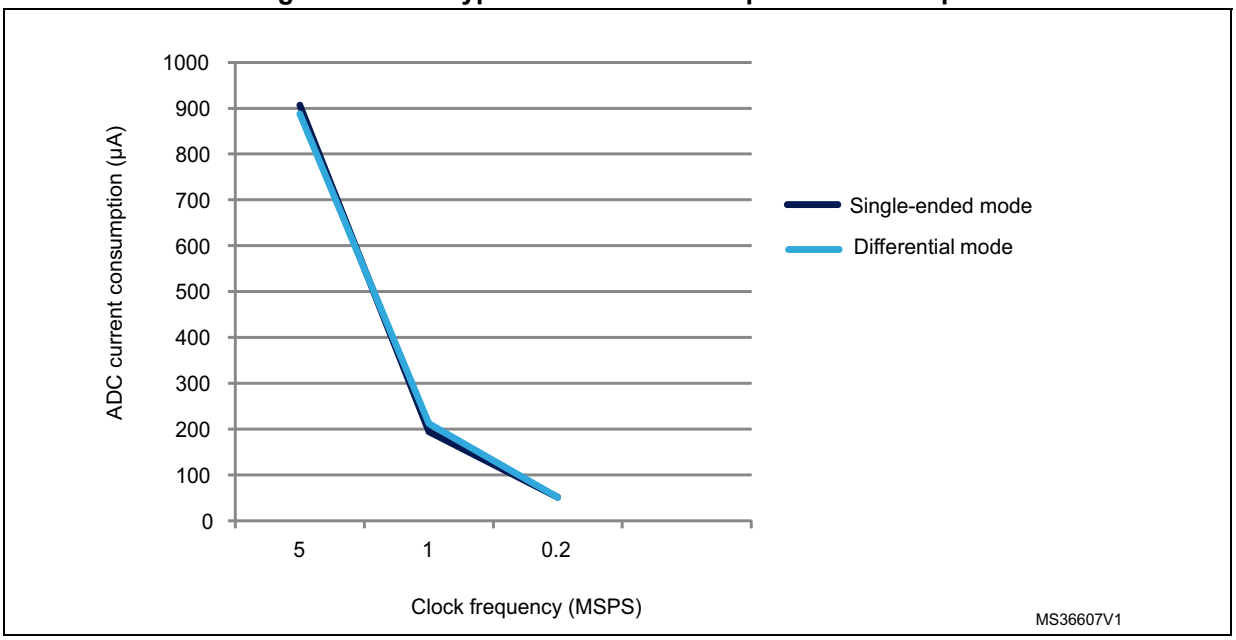


Figure 33. ADC typical current consumption on VREF+ pin

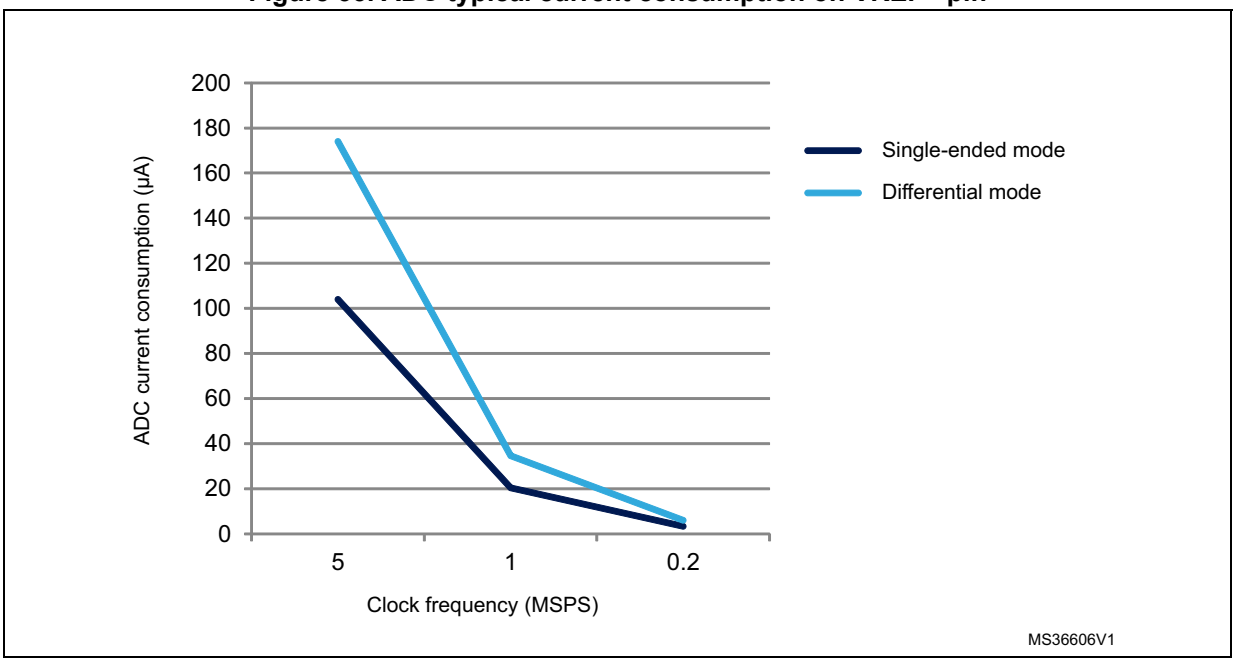


Table 71. ADC accuracy, 100-pin packages(1)(2)(3)

Symbol	Parameter	Conditions			Min (4)	Max(4)	Unit
ET	Total unadjusted error	ADC clock freq. ≤ 72 MHz, Sampling freq. ≤ 5 Msps 2 V ≤ V_{DDA} , V_{REF+} ≤ 3.6 V 100-pin package	Single Ended	Fast channel 5.1 Ms	-	±6.5	LSB
				Slow channel 4.8 Ms	-	±6.5	
			Differential	Fast channel 5.1 Ms	-	±4	
				Slow channel 4.8 Ms	-	±4	
EO	Offset error		Single Ended	Fast channel 5.1 Ms	-	±3	
				Slow channel 4.8 Ms	-	±3	
			Differential	Fast channel 5.1 Ms	-	±2	
				Slow channel 4.8 Ms	-	±2	
EG	Gain error		Single Ended	Fast channel 5.1 Ms	-	±6	
				Slow channel 4.8 Ms	-	±6	
			Differential	Fast channel 5.1 Ms	-	±3	
				Slow channel 4.8 Ms	-	±3	
ED	Differential linearity error		Single Ended	Fast channel 5.1 Ms	-	±1.5	
				Slow channel 4.8 Ms	-	±1.5	
			Differential	Fast channel 5.1 Ms	-	±1.5	
				Slow channel 4.8 Ms	-	±1.5	
EL	Integral linearity error		Single Ended	Fast channel 5.1 Ms	-	±2	
				Slow channel 4.8 Ms	-	±3	
			Differential	Fast channel 5.1 Ms	-	±2	
				Slow channel 4.8 Ms	-	±2	
ENOB (5)	Effective number of bits		Single Ended	Fast channel 5.1 Ms	10.4	-	bits
				Slow channel 4.8 Ms	10.2	-	
			Differential	Fast channel 5.1 Ms	10.8	-	
				Slow channel 4.8 Ms	10.8	-	

Table 72. ADC accuracy - limited test conditions, 64-pin packages(1)(2) (continued)

Symbol	Parameter	Conditions			Min (3)	Typ	Max (3)	Unit
SNR(4)	Signal-to-noise ratio	ADC clock freq. ≤ 72 MHz Sampling freq ≤ 5 Msps V_{DDA} = 3.3 V 25°C 64-pin package	Single ended	Fast channel 5.1 Ms	66	67	-	dB
				Slow channel 4.8 Ms	66	67	-	
			Differential	Fast channel 5.1 Ms	69	70	-	
				Slow channel 4.8 Ms	69	70	-	
THD(4)	Total harmonic distortion		Single ended	Fast channel 5.1 Ms	-	-80	-80	
				Slow channel 4.8 Ms	-	-78	-77	
			Differential	Fast channel 5.1 Ms	-	-83	-82	
				Slow channel 4.8 Ms	-	-81	-80	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.14* does not affect the ADC accuracy.
3. Guaranteed by characterization results.
4. Value measured with a -0.5 dB full scale 50 kHz sine wave input signal.

6.3.20 Comparator characteristics

Table 76. Comparator characteristics(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	-		2	-	3.6	V
V_{IN}	Comparator input voltage range	-		0	-	V_{DDA}	
V_{BG}	Scaler input voltage	-		-	1.2	-	
V_{SC}	Scaler offset voltage	-		-	±5	±10	mV
t_{S_SC}	V_{REFINT} scaler startup time from power down	First V_{REFINT} scaler activation after device power on		-	-	1(2)	s
		Next activations		-	-	0.2	ms
t_{START}	Comparator startup time	Startup time to reach propagation delay specification		-	-	60	µs
t_D	Propagation delay for 200 mV step with 100 mV overdrive	Ultra-low-power mode		-	2	4.5	µs
		Low-power mode		-	0.7	1.5	
		Medium power mode		-	0.3	0.6	
		High speed mode	$V_{DDA} \geq 2.7$ V	-	50	100	ns
			$V_{DDA} < 2.7$ V	-	100	240	
	Propagation delay for full range step with 100 mV overdrive	Ultra-low-power mode		-	2	7	µs
		Low-power mode		-	0.7	2.1	
		Medium power mode		-	0.3	1.2	
		High speed mode	$V_{DDA} \geq 2.7$ V	-	90	180	ns
			$V_{DDA} < 2.7$ V	-	110	300	
V_{offset}	Comparator offset error	-		-	±4	±10	mV
dV_{offset}/dT	Offset error temperature coefficient	-		-	18	-	µV/°C
$I_{DD(COMP)}$	COMP current consumption	Ultra-low-power mode		-	1.2	1.5	µA
		Low-power mode		-	3	5	
		Medium power mode		-	10	15	
		High speed mode		-	75	100	

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 115 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 9 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

P_{INTmax} = 20 mA × 3.5 V= 70 mW

P_{IOmax} = 9 × 8 mA × 0.4 V = 28.8 mW

This gives: P_{INTmax} = 70 mW and P_{IOmax} = 28.8 mW:

P_{Dmax} = 70 + 28.8 = 98.8 mW

Thus: P_{Dmax} = 98.8 mW

Using the values obtained in *Table 86* T_{Jmax} is calculated as follows:

– For LQFP100, 41°C/W

T_{Jmax} = 115 °C + (41°C/W × 98.8 mW) = 115 °C + 4.05 °C = 119.05 °C

This is within the range of the suffix 7 version parts (–40 < T_J < 125 °C).

In this case, parts must be ordered at least with the temperature range suffix 7 (see *Section 8: Ordering information*).